

Fig. 1A

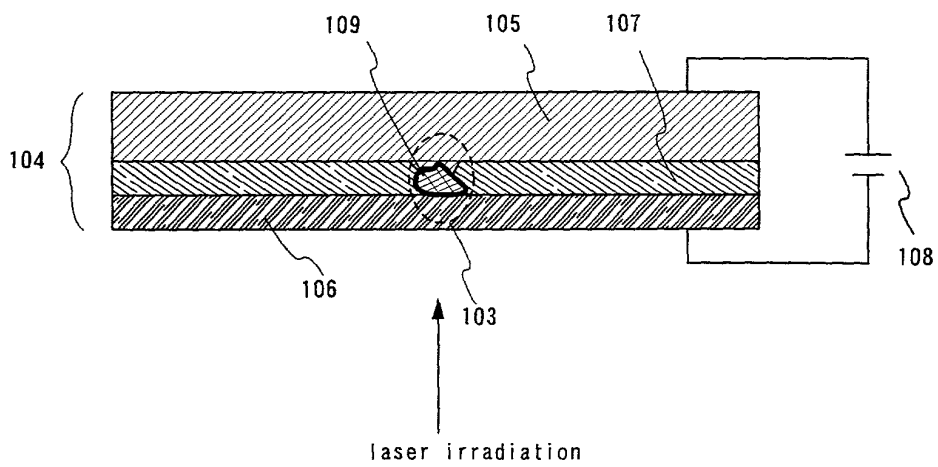


Fig. 1B

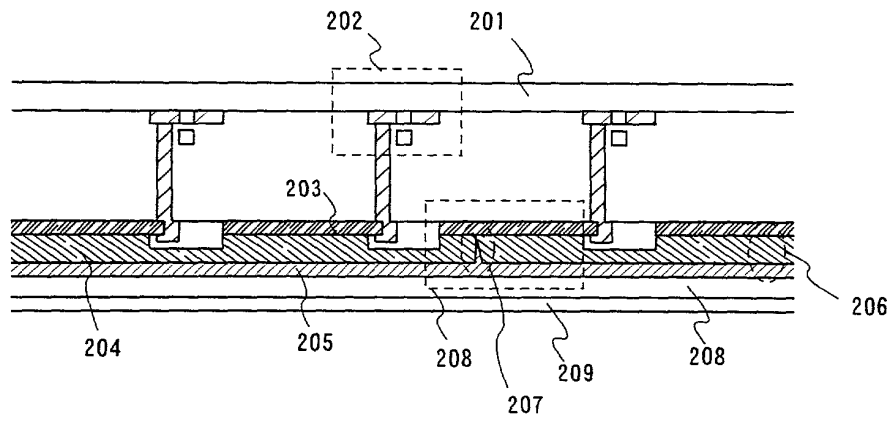


Fig. 2A

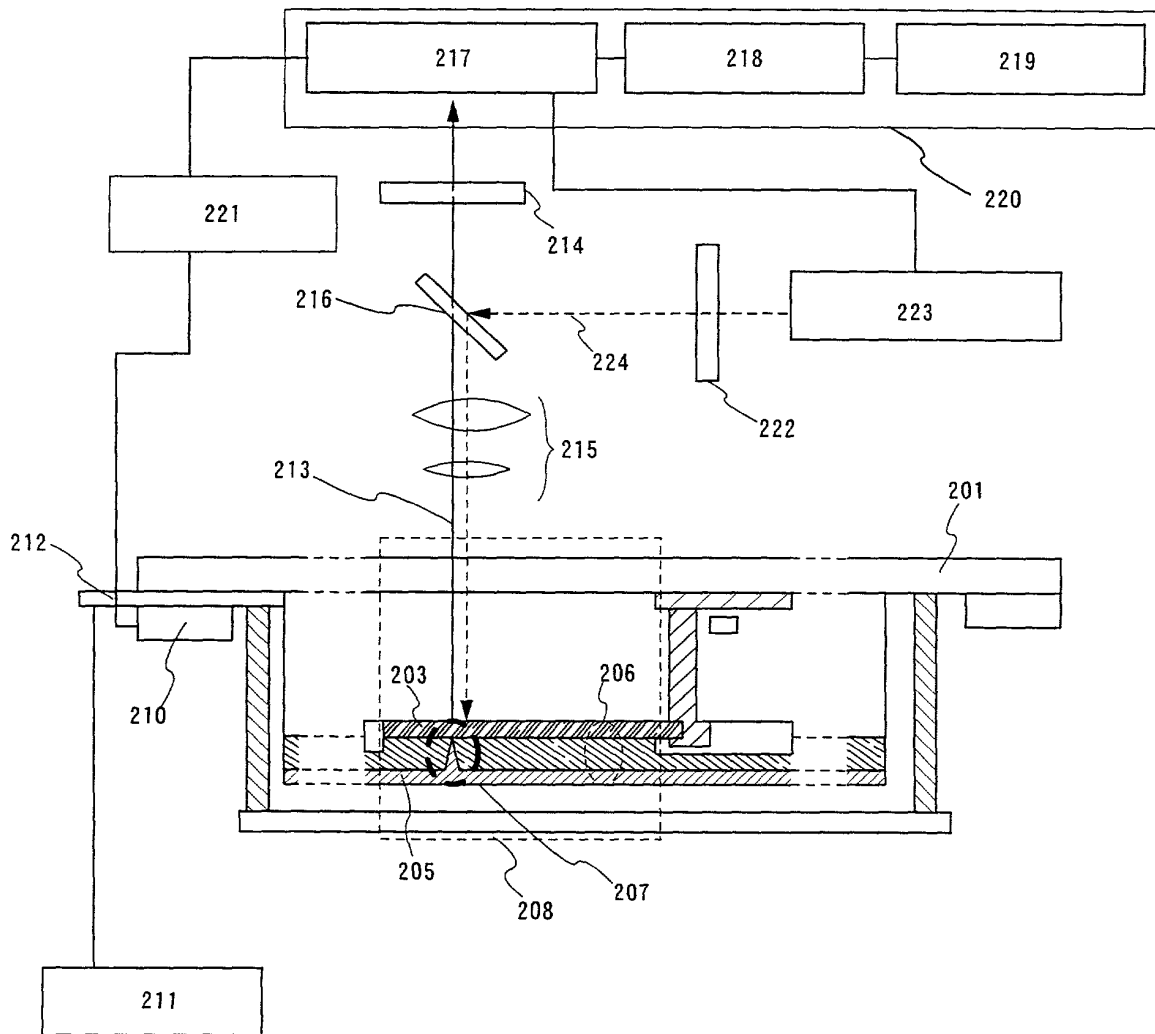


Fig. 2B

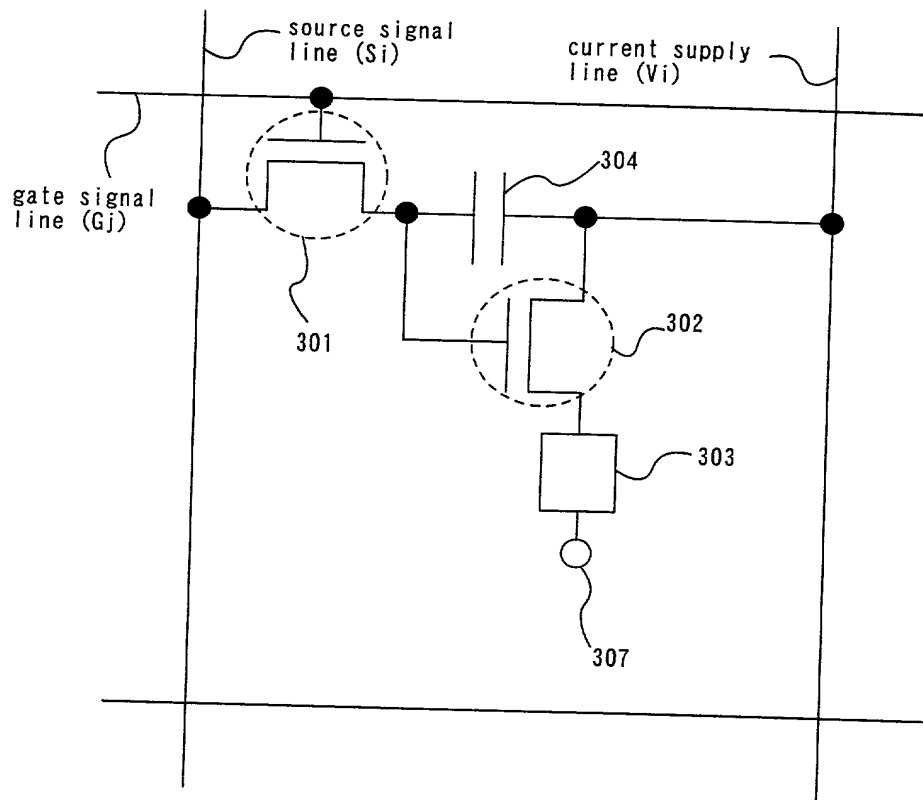
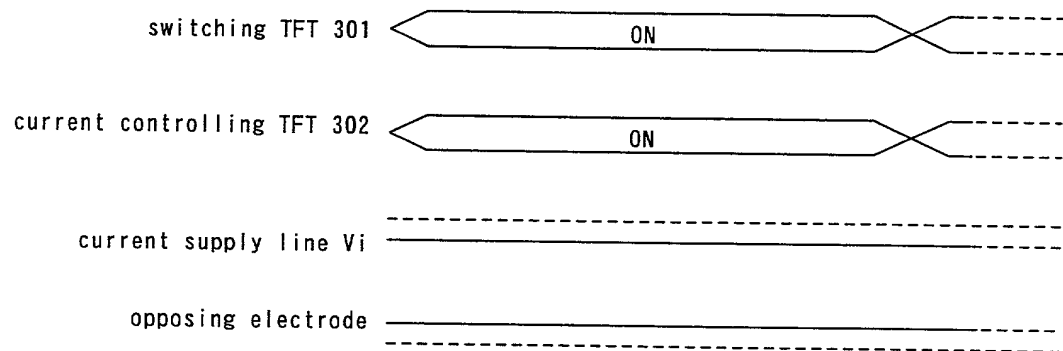
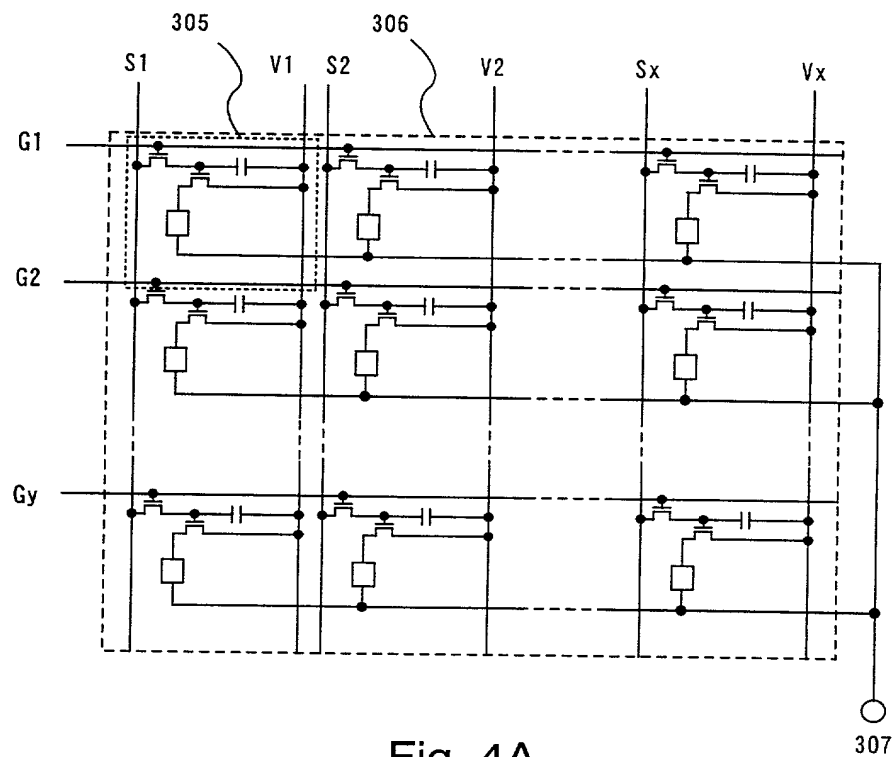
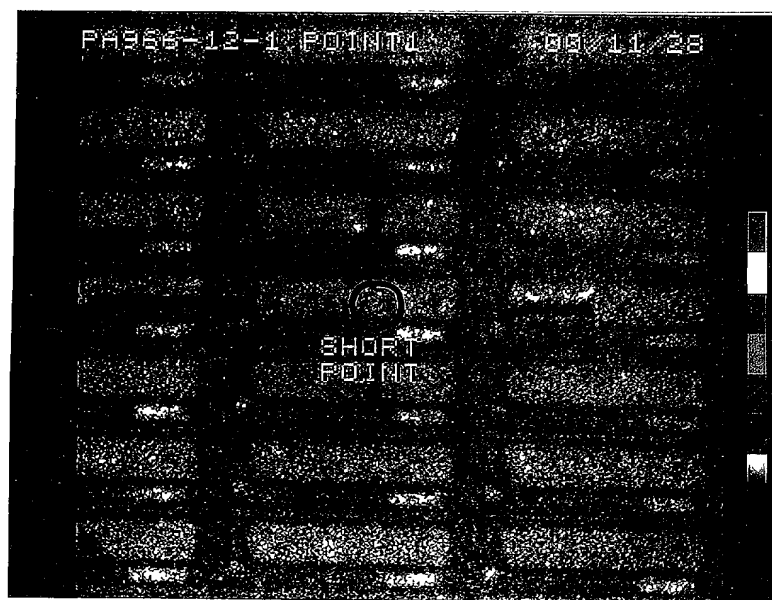


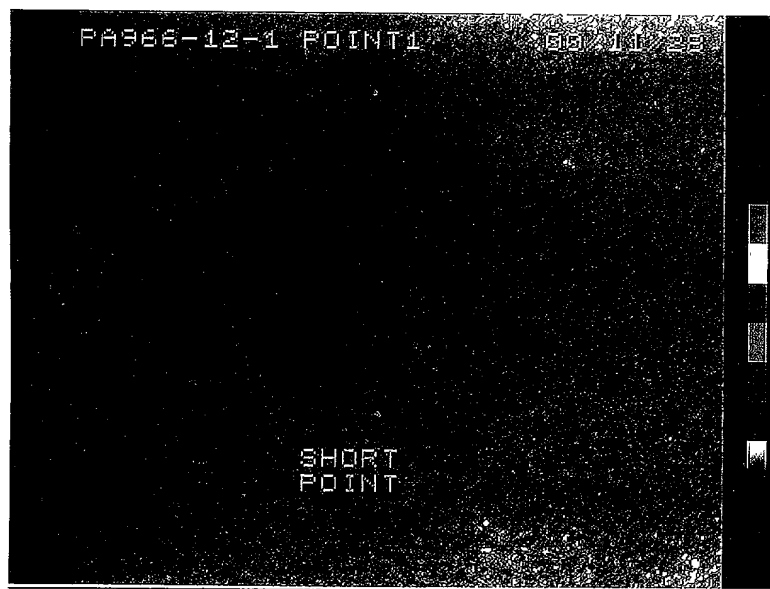
Fig. 3





×200

Fig. 5A



×500

Fig. 5B

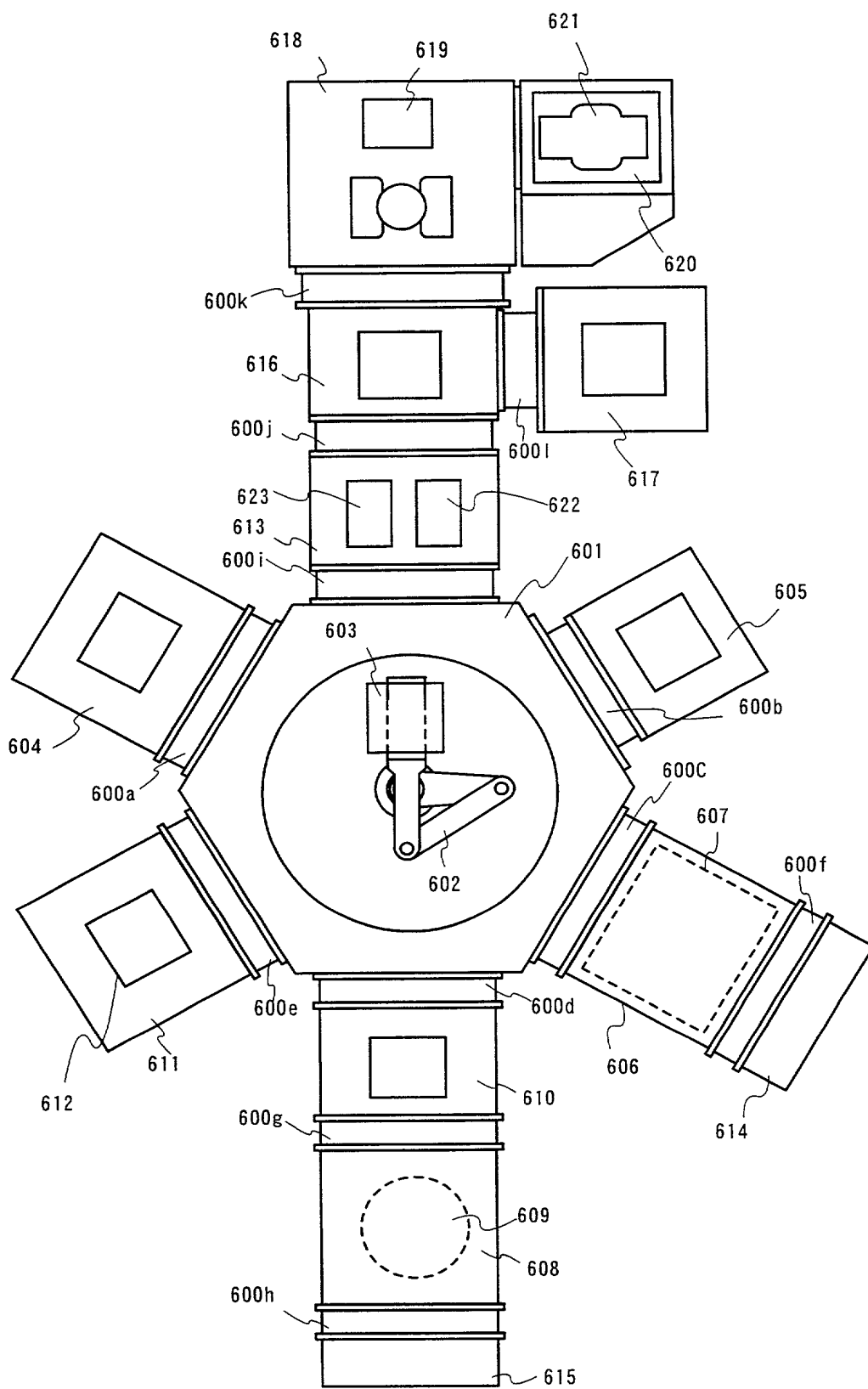


Fig. 6

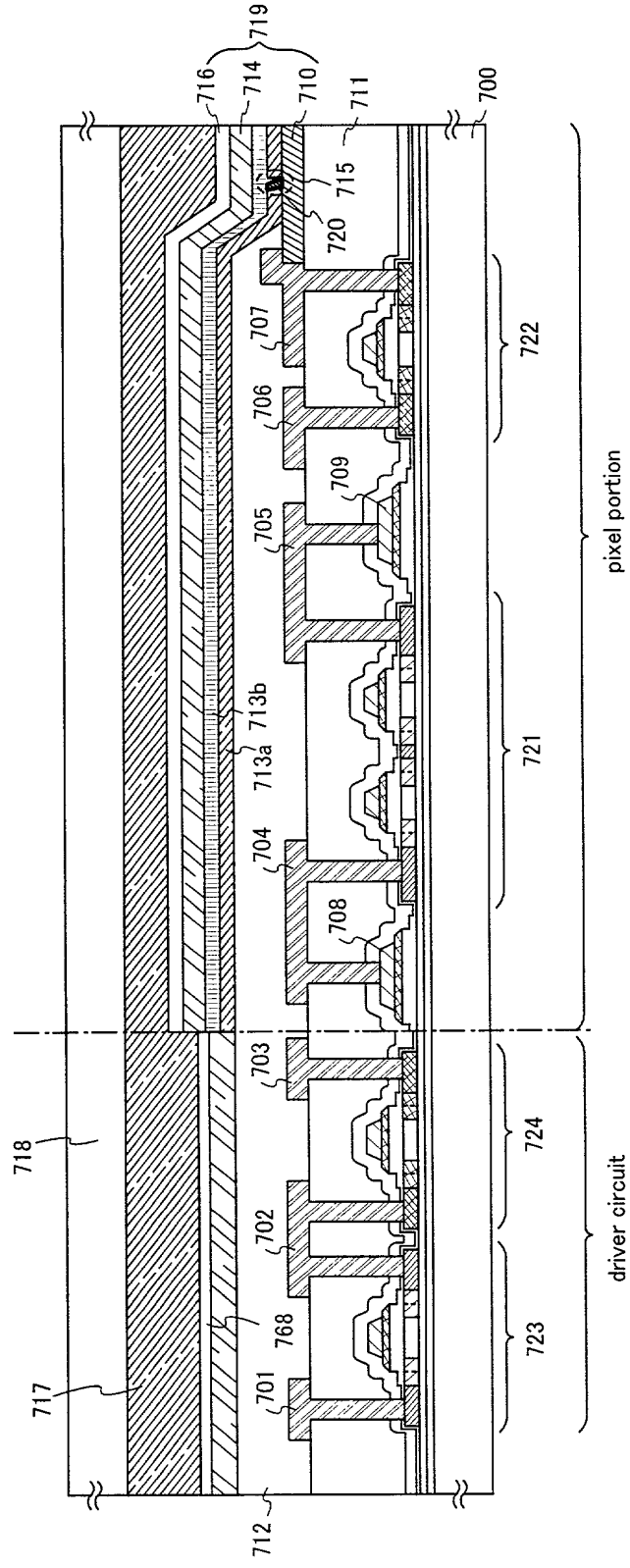
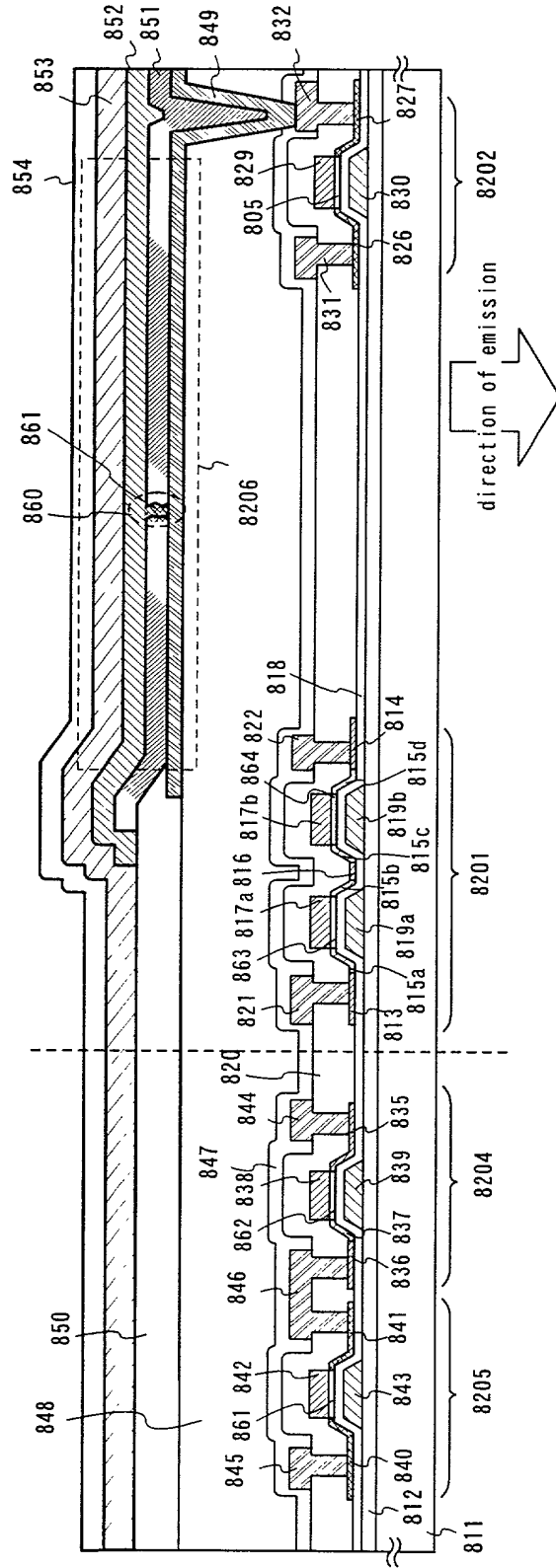


Fig. 7



811: substrate 812: base film 813: source region 814: drain region 815a~815d: LDD region 816: separation region 817a, 17b: channel formation region 818: gate insulating film 819a, 819b: gate electrodes 820: first interlayer insulating film 821: source signal line 822: drain wiring 826: source region 827: drain region 828: LDD region 829: channel formation region 830: gate electrode 831: source wiring 832: drain wiring 835: source region 836: drain region 837: LDD region 838: channel formation region 839: gate electrode 840: source region 841: drain region 842: channel formation region 843: gate electrode 844, 845: source wirings 846: drain wiring 847: first passivation film 848: second interlayer insulating film 849: pixel electrode (anode) 850: third interlayer insulating film 851: organic compound layer 852: cathode 853: protecting electrode 854: second passivation film

Fig. 8



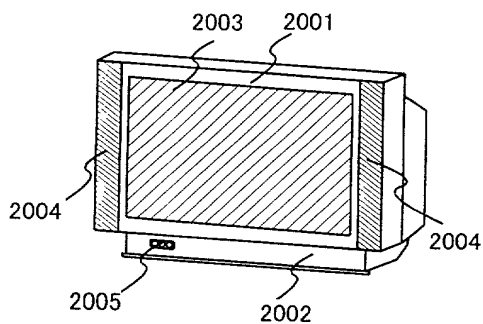


Fig. 9A

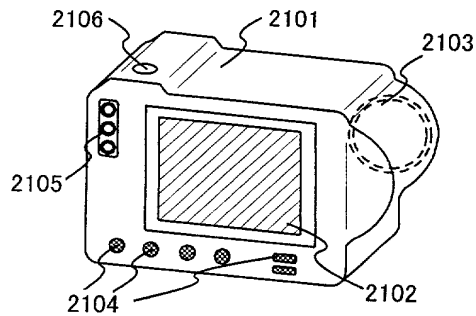


Fig. 9B

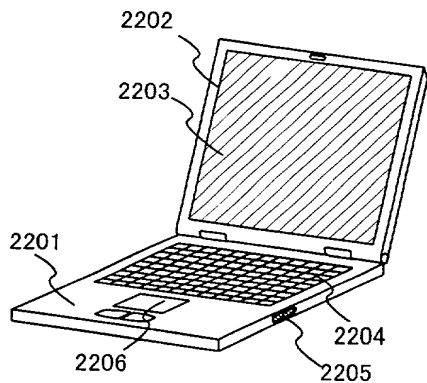


Fig. 9C

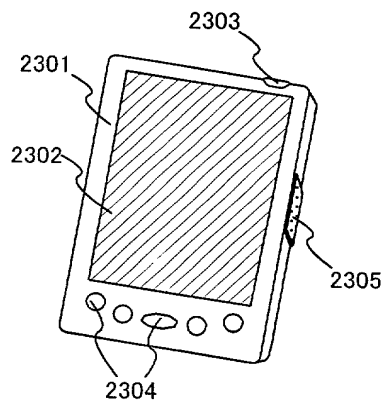


Fig. 9D

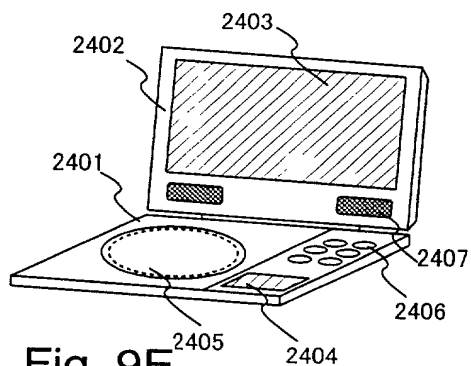


Fig. 9E

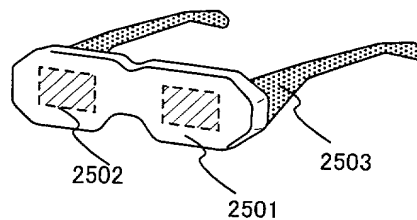


Fig. 9F

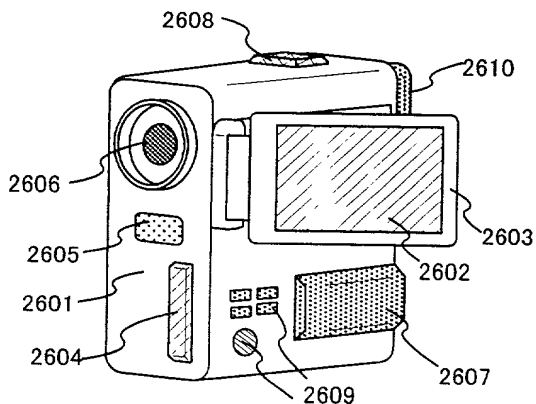


Fig. 9G

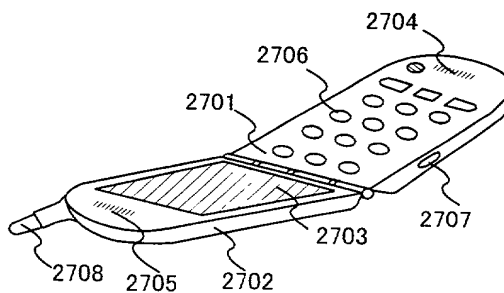


Fig. 9H

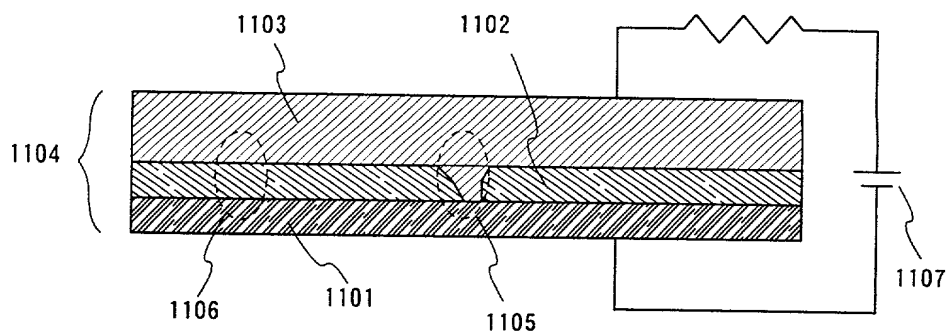


Fig. 10A

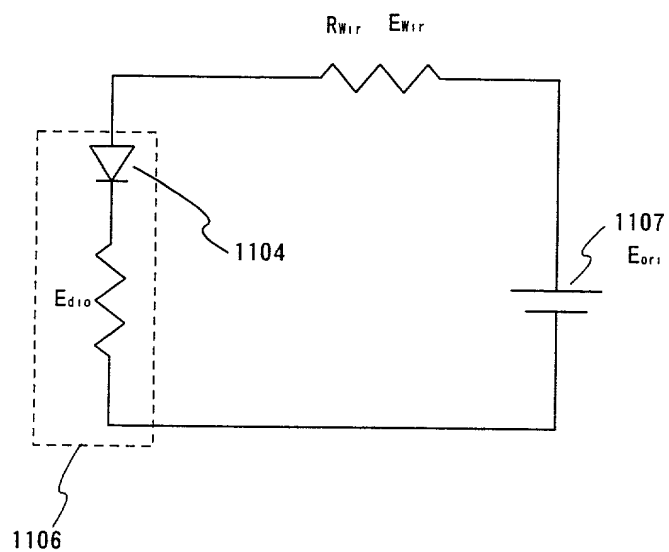


Fig. 10B

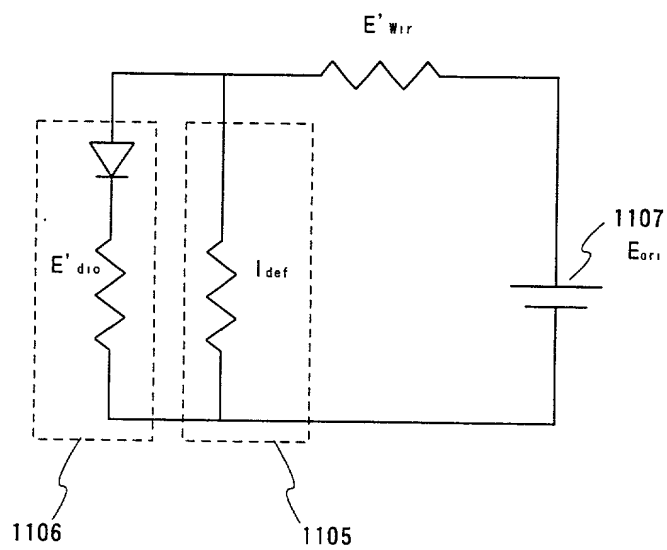


Fig. 10C

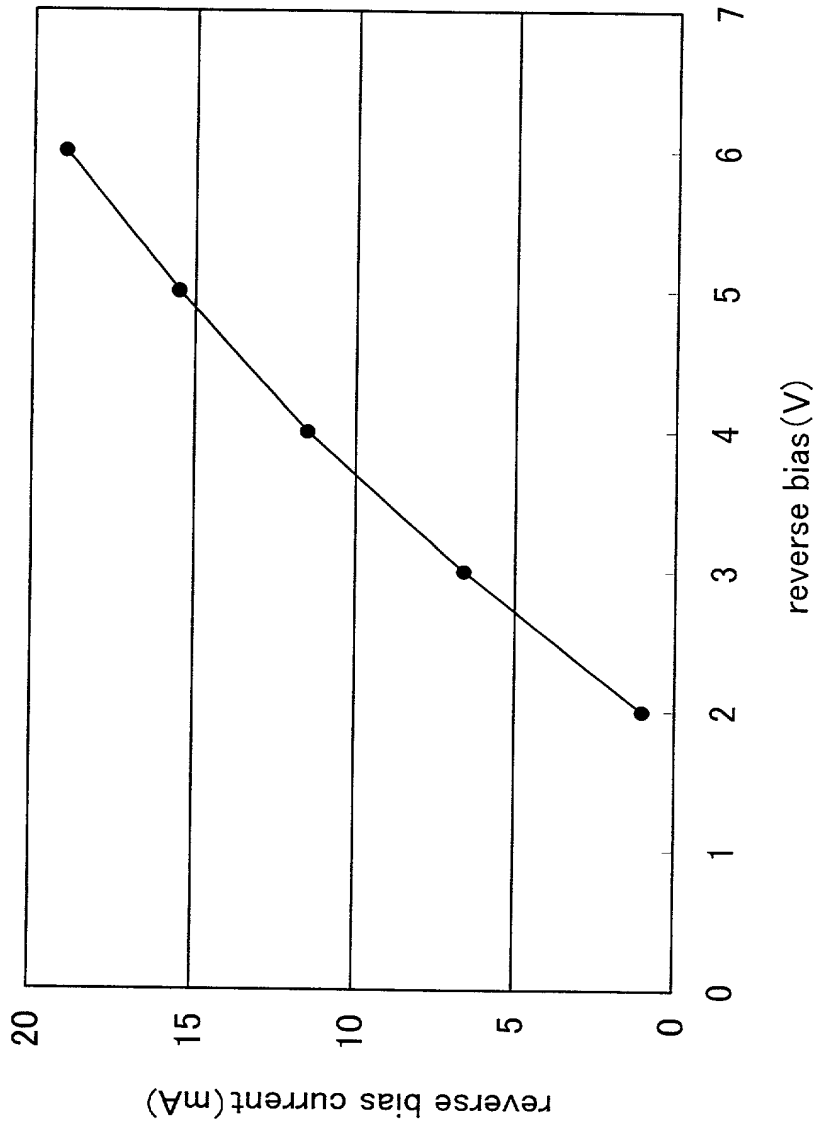


Fig. 11 Current property when a backward bias voltage is applied to a light emitting element